

L Number	Hits	Search Text	DB	Time stamp
1	1	6037712.pn.	USPAT; US-PGPUB	2003/07/12 17:54
-	65	((TFT transistor) and ((insulat\$3 dielectric) same (SIN SION (silicon near2 (nitride oxynitride)))) and ((organic near2 (element layer film electroluminescen\$2 EL)) (light near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer) and 313/498-512.ccls.	USPAT; US-PGPUB	2003/07/12 10:47
-	302	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 (element layer film electroluminescen\$2 EL)) (light near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer) and 313/495-512.ccls.	USPAT; US-PGPUB	2003/07/01 10:46
-	2	("4266223" "5384517").PN.	USPAT	2003/06/30 16:29
-	17	5640067.URPN.	USPAT	2003/06/30 16:29
-	10	("5247190" "5306651" "5399502" "5594569" "5640067" "5643826" "5731613" "5897328" "5923962" "6048758" "2001/0004121").PN.	USPAT	2003/06/30 16:39
-	2	6461899.URPN.	USPAT	2003/06/30 16:43
-	246	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 (element layer film electroluminescen\$2 EL)) (light near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer) and 313/495-512.ccls.) not @ad>20011108	USPAT; US-PGPUB	2003/07/01 11:00
-	1620	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 (element layer film electroluminescen\$2 EL)) (light near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer) and 257/\$.ccls.) not @ad>20001110	USPAT; US-PGPUB	2003/07/01 11:03
-	5408	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 (element layer film electroluminescen\$2 EL)) (light near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer)) not @ad>20001110	USPAT; US-PGPUB	2003/07/01 11:16
-	73816	257/\$4.ccls.	USPAT; US-PGPUB	2003/07/01 11:06
-	999	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 (element layer film electroluminescen\$2 EL)) (light near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer)) not @ad>20001110) and 257/\$4.ccls.	USPAT; US-PGPUB	2003/07/01 11:06
-	927	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 ((light near2 (emitting emission emitter)) electroluminescen\$2 EL)) (light near3 (layer element film) near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer)) not @ad>20001110	USPAT; US-PGPUB	2003/07/01 12:38
-	77791	313/495-512.ccls. 257/\$3.ccls.	USPAT; US-PGPUB	2003/07/01 11:56
-	361	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 ((light near2 (emitting emission emitter)) electroluminescen\$2 EL)) (light near3 (layer element film) near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer)) not @ad>20001110) and (313/495-512.ccls. 257/\$3.ccls.)	USPAT; US-PGPUB	2003/07/01 11:56
-	8	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2 ((light near2 (emitting emission emitter)) electroluminescen\$2 EL)) (light near3 (layer element film) near2 (emitting emission emitter)))) and (partition rampart ridge rib barrier wall spacer)) not @pd>20001110	EPO; JPO; DERWENT	2003/07/01 12:41
-	22	((TFT transistor) same (insulat\$3 insolat\$3 isolat\$3 dielectric)) and ((EL electroluminescen\$2 (light near2 (emitting emission emitter)))) near3 (device display panel element)) and (partition barrier rib spacer rampart wall)	EPO; JPO; DERWENT	2003/07/03 16:02
-	685	((TFT transistor) same (insulat\$3 insolat\$3 isolat\$3 dielectric)) and ((EL electroluminescen\$2 (light near2 (emitting emission emitter)))) near3 (device display panel element)) and (partition barrier rib spacer rampart wall) and (313/495-512.ccls. 257/\$3.ccls.)	USPAT; US-PGPUB	2003/07/03 17:15

-	369	((TFT transistor) same (insulat\$3 insulat\$3 isolat\$3 dielectric)) and ((EL electroluminescen\$2 (light near2 (emitting emission emitter))) near3 (device display panel element)) and (partition barrier rib spacer rampart wall) and (313/495-512.ccls. 257/\$3.ccls.)) not @ad>20001110	USPAT; US-PGPUB	2003/07/03 16:46
-	24	("4774556" "4780424" "4861730" "4929988" "5017977" "5021848" "5053842" "5071782" "5078498" "5146426" "5202576" "5323042" "5350937" "5594569" "5633519" "5643826" "5923962" "5939731" "5965915" "6055034" "6166414" "6172671" "6198133" "6281552").PN.	USPAT	2003/07/03 16:36
-	2133	semiconductor adj energy adj laboratory\$.as.	USPAT; US-PGPUB	2003/07/03 16:45
-	211	((TFT transistor) same (insulat\$3 insulat\$3 isolat\$3 dielectric)) and ((EL electroluminescen\$2 (light near2 (emitting emission emitter))) near3 (device display panel element)) and (partition barrier rib spacer rampart wall) and (313/495-512.ccls. 257/\$3.ccls.)) not @pd>20001110	USPAT; US-PGPUB	2003/07/03 16:47
-	2	("5742129" "5804917").PN.	USPAT	2003/07/03 17:16
-	2	("5631664" "5684365").PN.	USPAT	2003/07/03 17:17
-	59	5684365.URPN.	USPAT	2003/07/03 17:17
-	1118	313/504.ccls.	USPAT; US-PGPUB	2003/07/03 17:18
-	6	("4015166" "5550066" "5684365" "5742129" "6072450" "6091382").PN.	USPAT	2003/07/03 17:19
-	204	313/504.ccls. and transistor	USPAT; US-PGPUB	2003/07/07 10:37
-	5	("4734623" "5518808" "5565742" "5859508" "5936347").PN.	USPAT	2003/07/07 10:34
-	3	("5352543" "5371434" "5384517").PN.	USPAT	2003/07/07 10:35
-	1	"5156924".PN.	USPAT	2003/07/07 10:36
-	11	5352543.URPN.	USPAT	2003/07/07 10:36
-	478	313/498-512.ccls. and transistor	USPAT; US-PGPUB	2003/07/07 10:37
-	122	313/504.ccls. and TFT	USPAT; US-PGPUB	2003/07/07 10:42
-	4	("5004950" "5194290" "5523770" "5804917").PN.	USPAT	2003/07/07 10:41
-	581	313/504.ccls. and (carbon diamond graphite)	USPAT; US-PGPUB	2003/07/07 10:42
-	280	313/504.ccls. and ((carbon diamond graphite) with (dielectric insulat\$3 layer film coat\$3))	USPAT; US-PGPUB	2003/07/07 10:48
-	4	("5004950" "5194290" "5523770" "5804917").PN.	USPAT	2003/07/07 10:46
-	3	6114183.URPN.	USPAT	2003/07/07 10:46
-	445	345/92.ccls.	USPAT; US-PGPUB	2003/07/07 10:48
-	65	345/92.ccls. and (((organic near3 (EL electroluminescen\$2)) (light near2 (emitting emission emitter))) near3 (element device display panel))	USPAT; US-PGPUB	2003/07/07 11:00
-	366	345/76-81.ccls. and (((organic near3 (EL electroluminescen\$2)) (light near2 (emitting emission emitter))) near3 (element device display panel))	USPAT; US-PGPUB	2003/07/07 11:04
-	79	345/76-81.ccls. and (((organic near3 (EL electroluminescen\$2)) (light near2 (emitting emission emitter))) near3 (element device display panel)) and (rampart barrier rib spacer partition ridge)	USPAT; US-PGPUB	2003/07/07 11:05
-	340	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (element layer film)) and 313/500-512.ccls.	USPAT; US-PGPUB	2003/07/12 13:24
-	1010	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (element layer film)) and 257/\$.ccls.	USPAT; US-PGPUB	2003/07/12 11:39

-	784	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (element layer film)) and 257/\$3.ccls.	USPAT; US-PGPUB	2003/07/12 11:42
-	481	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (element layer film)) and (organic OLED) and 257/\$3.ccls.	USPAT; US-PGPUB	2003/07/12 11:43
-	228	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (OLED organic) near2 (element layer film)) and 257/\$3.ccls.	USPAT; US-PGPUB	2003/07/12 12:04
-	3	("5294870" "5552547" "5641611").PN.	USPAT	2003/07/12 11:51
-	172	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (OLED organic) near2 (element layer film)) and 345/\$3.ccls.	USPAT; USPAT; US-PGPUB	2003/07/12 12:06
-	0	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (OLED organic) near2 (element layer film)) and 169.3/\$3.ccls.	USPAT; US-PGPUB	2003/07/12 12:06
-	134	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (OLED organic) near2 (element layer film)) and 438/\$3.ccls.	USPAT; US-PGPUB	2003/07/12 12:07
-	162	((insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (OLED organic) near2 (element layer film)) and 345/\$3.ccls.) not ((insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (OLED organic) near2 (element layer film)) and 257/\$3.ccls.)	USPAT; US-PGPUB	2003/07/12 12:07
-	784	(DLC diamond-like (diamond near2 like) carbon) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (element layer film)) and 313/500-512.ccls.	USPAT; US-PGPUB	2003/07/12 13:26
-	520	(DLC diamond-like (diamond near2 like) carbon) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (organic OLED) near2 (element layer film)) and 313/500-512.ccls.	USPAT; US-PGPUB	2003/07/12 13:26
-	1	5952708.pn.	USPAT; US-PGPUB	2003/07/12 13:39
-	62	((insulat\$3 dielectric) same (DLC diamond-like carbide (diamond near2 like) carbon)) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (organic OLED) near2 (element layer film)) and 313/500-512.ccls.	USPAT; USPAT; US-PGPUB	2003/07/12 14:05
-	70	((protect\$3) same (DLC diamond-like carbide (diamond near2 like) carbon)) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (organic OLED) near2 (element layer film)) and 313/500-512.ccls.	USPAT; US-PGPUB	2003/07/12 14:30
-	9	("5276380" "5294869" "5521465" "5587589" "5652067" "5656508" "5693962" "5701055" "5773931").PN.	USPAT	2003/07/12 14:11
-	1	6037712.pn.	USPAT; US-PGPUB	2003/07/12 17:54